

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-19.(Canceled)

20.(Currently Amended) A semiconductor device having a thin film transistor, the thin film transistor comprising:

~~at least one thin film transistor formed over a substrate, said thin film transistor comprising at least a semiconductor region, a gate electrode, and a gate insulating film interposed therebetween;~~

~~an interlayer insulating film formed over said thin film transistor;~~

~~a contact hole formed through said interlayer insulating film; and~~

~~a wiring electrically connected with said semiconductor region in said contact hole, wherein said wiring contains germanium at a concentration from 20 to 40 atomic%~~

a semiconductor layer on an insulating surface, wherein the semiconductor layer has a side recessed portion;

a gate electrode adjacent to the semiconductor layer with a gate insulating film interposed therebetween; and

an electrode in contact with the semiconductor layer, wherein the electrode contains a first layer and a second layer, and

wherein the side recessed portion is filled with the first layer.

21-27.(Canceled)

28.(New) The semiconductor device having a thin film transistor according to claim 20, wherein the semiconductor layer contains crystalline silicon.

29.(New) The semiconductor device having a thin film transistor according to claim 20, wherein the first layer contains at least one selected from the group consisting of germanium, tin, gallium, zinc, lead, indium, and antimony.

30.(New) The semiconductor device having a thin film transistor according to claim 20, wherein the first layer is an alloy of aluminum and germanium.

31.(New) The semiconductor device having a thin film transistor according to claim 20, wherein the second layer contains aluminum.

32.(New) The semiconductor device having a thin film transistor according to claim 20, wherein the electrode is a source electrode.

33.(New) The semiconductor device having a thin film transistor according to claim 20, wherein the semiconductor device is an active matrix type EL display device.

34.(New) A semiconductor device having a thin film transistor, the thin film transistor comprising:

- a semiconductor layer on an insulating surface, wherein the semiconductor layer has a first side recessed portion;

- a gate electrode adjacent to the semiconductor layer with a gate insulating film interposed therebetween, wherein the gate electrode has a second side recessed portion; and

- an electrode in contact with the semiconductor layer, wherein the electrode contains a first layer and a second layer, and

- wherein the first side recessed portion and the second side recessed portion are filled with the first layer.

35.(New) The semiconductor device having a thin film transistor according to claim 34, wherein the semiconductor layer contains crystalline silicon.

36.(New) The semiconductor device having a thin film transistor according to claim 34, wherein the first layer contains at least one selected from the group consisting of germanium, tin, gallium, zinc, lead, indium, and antimony.

37.(New) The semiconductor device having a thin film transistor according to claim 34, wherein the first layer is an alloy of aluminum and germanium.

38.(New) The semiconductor device having a thin film transistor according to claim 34, wherein the second layer contains aluminum.

39.(New) The semiconductor device having a thin film transistor according to claim 34, wherein the electrode is a source electrode.

40.(New) The semiconductor device having a thin film transistor according to claim 34, wherein the semiconductor device is an active matrix type EL display device.

41.(New) A semiconductor device having a thin film transistor, the thin film transistor comprising:

- a semiconductor layer on an insulating surface, wherein the semiconductor layer has a side recessed portion;

- a gate insulating film on the semiconductor layer;

- a gate electrode on the gate insulating film;

- an interlayer insulating film over at least the gate electrode; and

- an electrode over the interlayer insulating film, wherein the electrode is in contact with the semiconductor layer through a contact hole opened in the interlayer insulating film, wherein the electrode contains a first layer and a second layer, and

- wherein the side recessed portion is filled with the first layer.

42.(New) The semiconductor device having a thin film transistor according to claim 41, wherein the semiconductor layer contains crystalline silicon.

43.(New) The semiconductor device having a thin film transistor according to claim 41, wherein the first layer contains at least one selected from the group consisting of germanium, tin, gallium, zinc, lead, indium, and antimony.

44.(New) The semiconductor device having a thin film transistor according to claim 41, wherein the first layer is an alloy of aluminum and germanium.

45.(New) The semiconductor device having a thin film transistor according to claim 41, wherein the second layer contains aluminum.

46.(New) The semiconductor device having a thin film transistor according to claim 41, wherein the electrode is a source electrode.

47.(New) The semiconductor device having a thin film transistor according to claim 41, wherein the interlayer insulating film contains at least one selected from the group consisting of silicon oxide, silicon nitride and silicon oxynitride.

48.(New) The semiconductor device having a thin film transistor according to claim 41, wherein the semiconductor device is an active matrix type EL display device.

49.(New) A semiconductor device having a thin film transistor, the thin film transistor comprising:

a semiconductor layer on an insulating surface, wherein the semiconductor layer has a first side recessed portion;

a gate insulating film on the semiconductor layer;

a gate electrode on the gate insulating film, wherein the gate electrode has a second side recessed portion;

an interlayer insulating film over at least the gate electrode; and

an electrode over the interlayer insulating film, wherein the electrode is in contact with the semiconductor layer through a contact hole opened in the interlayer insulating film, wherein the electrode contains a first layer and a second layer, and

wherein the first side recessed portion and the second side recessed portion are filled with the first layer.

50.(New) The semiconductor device having a thin film transistor according to claim 49, wherein the semiconductor layer contains crystalline silicon.

51.(New) The semiconductor device having a thin film transistor according to claim 49, wherein the first layer contains at least one selected from the group consisting of germanium, tin, gallium, zinc, lead, indium, and antimony.

52.(New) The semiconductor device having a thin film transistor according to claim 49, wherein the first layer is an alloy of aluminum and germanium.

53.(New) The semiconductor device having a thin film transistor according to claim 49, wherein the second layer contains aluminum.

54.(New) The semiconductor device having a thin film transistor according to claim 49, wherein the electrode is a source electrode.

55.(New) The semiconductor device having a thin film transistor according to claim 49, wherein the interlayer insulating film contains at least one selected from the group consisting of silicon oxide, silicon nitride and silicon oxynitride.

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56.(New) The semiconductor device having a thin film transistor according to claim 49,
wherein the semiconductor device is an active matrix type EL display device.